

MP27931

5kV_{RMS} Quad Channels Digital Isolator Channel Direction: 3 Forward 1 Reverse

PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

DESCRIPTION

The MP27931 is a high performance four-channel digital isolator designed for robust applications. This device can survive a $5000V_{\text{RMS}}$ isolation rating per UL 1577. This device is optimized for replacing opto-couplers and can support a high data rate of up to 150Mbps. This product can maintain its performance over a wide temperature range while minimizing power consumption.

The MP27931 uses capacitive isolation technology, to support up to 5kVrms insulation voltage rating. This device includes safety-related certifications according to UL 1577, VDE, CSA, as well as CQC. This isolator provides small size, low-power-consumption and higher reliability operation compared to traditional opto-coupler isolator.

This device provides schmitt trigger input and isolated encoding/decoding for high electromagnetic immunity in noisy environments. High/Low selectable fail-safe output supports fixed output even if the input signal power fails. This product is part of a family of quad channel digital isolators which can have 2-4 forward channels and 0-2 reverse channels for a total of four channels.

The MP27931 is available in a wide-body SOIC-16 WB package.

FEATURES

- Channel Direction: 3 Forward 1 Reverse
- 5kV_{RMS} Isolation Voltage
- Support DC to 150Mbps Data Rate
- 2.5V to 5.5V Operation Range
- >±100kV/µs Common-mode Transient Immunity (CMTI)
- High System Level ESD, EFT, Surge Immunity Performance
- 13ns Propagation Delay for 5V Operation
- Ultra Low Power Supply Current
- Default Output Logic High (MP27931) and Low (MP27931-L) Options
- Tri-state Outputs with EN Control
- 1.2kV Peak V_{IORM} Working Insulation
- Wide Temperature Range: -40°C to +125°C
- Available in SOIC-16 WB Package
- UL 1577 recognized
 - SOIC-16 WB Up to 5000 V_{RMS} for 1 minute
- CSA Component Notice 5A Approval
- DIN EN IEC 60747-17 (VDE 0884-17): 2021-10 Certified (In Progress)
 - SOIC-16 WB: 7071 V_{PK} Isolation
- CQC Certification per GB4943.1-2011 (In Progress)

APPLICATIONS

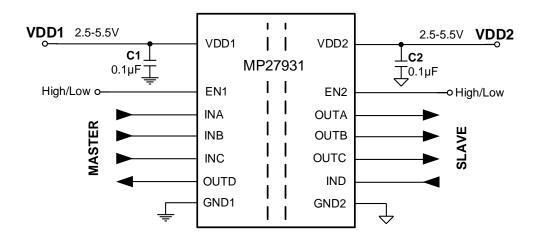
- Industrial Automation
- Isolated ADC/DAC
- Motor Controller and Driver
- Solar Inverters
- Isolated switch mode supplies
- Medical Equipment

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TYPICAL APPLICATION





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ORDERING INFORMATION

Part Number*	Output Default	Package	Top Marking	MSL Rating
MP27931GY	HIGH	SOIC-16 WB	See Below	TBD
MP27931-LGY	LOW	301C-10 WB	See below	טפו

^{*} For Tape & Reel, add suffix -Z (e.g. MP27931GY-Z).

TOP MARKING

MP27931GY (SOIC-16 WB, Default HIGH)

MPSYYWW MP27931 LLLLLLLL

MPS: MPS prefix YY: Year code WW: Week code MP27931: Part number

LLLLLLL: Lot number

TOP MARKING

MP27931-LGY (SOIC-16 WB, Default LOW)

MPS YYWW MP27931-L LLLLLLLL

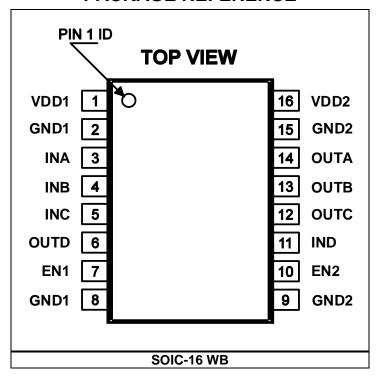
MPS: MPS prefix YY: Year code WW: Week code

MP27931-L: Part number LLLLLLL: Lot number



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

PACKAGE REFERENCE





PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

PIN FUNCTIONS

Pin #	Name	Description
1	VDD1	Side 1 power supply pin. It is recommended to connect a 0.1µF decoupling capacitor between this pin and GND1 (pin2).
2, 8	GND1	Side 1 ground pin.
3	INA	Channel A input pin.
4	INB	Channel B input pin.
5	INC	Channel C input pin.
6	OUTD	Channel D output pin.
7	EN1	Side 1 Output Port Enable Pin. Active High, internal pulled up in default. It is recommended that the enable inputs be connected to an external logic high or low level when the IC is operating in noisy environments. To minimize noise coupling, do not connect circuit traces to EN1 or EN2 if they are left floating.
9, 15	GND2	Side 2 ground pin.
10	EN2	Side 2 Output Port Enable Pin. Active High, internal pulled up in default. It is recommended that the enable inputs be connected to an external logic high or low level when the IC is operating in noisy environments. To minimize noise coupling, do not connect circuit traces to EN1 or EN2 if they are left floating.
11	IND	Channel D input pin.
12	OUTC	Channel C output pin.
13	OUTB	Channel B output pin.
14	OUTA	Channel A output pin.
16	VDD2	Side 2 power supply pin. It is recommended to connect a 0.1µF decoupling capacitor between this pin and GND2 (pin15).



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

ABSOLUTE MAXIMUM RATINGS (1) VDD1 to GND1, VDD2 to GND2
-0.3V to VDD1+0.3V ⁽²⁾ Side 2 other pins to GND2
-0.3V to VDD2+0.3V ⁽² -0.3V to VDD2+0.3V ⁽² -10mA to 10mA
Continuous power dissipation $(T_A = +25^{\circ}C)^{(3)}$ SOIC-16 WBTBDW ⁽⁵⁾
Junction temperature150°C Lead temperature260°C
Storage temperature65°C to +150°C ESD Ratings
Human body model (HBM)±6000V Charged device model (CDM)±2000V Isolation barrier withstand with HBM±8000V
Recommended Operating Conditions (4)
Supply voltage $V_{DD1},\ V_{DD2}$ 2.5V to 5.5V Maximum signal data rate DC to 150Mbps Operating junction temp. (T _J)40°C to +125°C

Thermal Resistance	$oldsymbol{ heta}_{JA}$	$oldsymbol{ heta}$ JC
SOIC-16 WB		
EV27931-Y-00A ⁽⁵⁾	. TBD .	TBD °C/W
JESD51-7 ⁽⁶⁾	. TBD .	TBD °C/W

Notes:

- Exceeding these ratings may damage the device.
- Maximum Voltage must not exceed 7.5V.
- The maximum allowable power dissipation is a function of the maximum junction temperature T_J (MAX), the junction-toambient thermal resistance θ_{JA} , and the ambient temperature T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by PD (MAX) = (TJ $(MAX)-T_A)/\theta_{JA}$. Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- Measured on EV27931-Y-00A, 2-layer, 63mm x 63mm PCB.
- The value of θ_{JA} given in this table is only valid for comparison with other packages and cannot be used for design purposes. These values were calculated in accordance with JESD51-7, and simulated on a specified JEDEC board. They do not represent the performance obtained in an actual application.



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

ELECTRICAL CHARACTERISTICS

 $V_{DD1} = V_{DD2} = 5V$, $T_J = -40$ °C to 125°C(7), typical values are tested at $T_J = 25$ °C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Switching Timing Characteristics				<u>'</u>		
Minimum Pulse Width					5	ns
Propagation Delay ⁽⁸⁾	t _{PLH} , t _{PHL}			13		ns
Pulse Width Distortion	PWD	t _{PLH} - t _{PHL}		1.5	4.5	ns
Propagation Delay Skew (9)	tPSK(P-P)				4.5	ns
Channel-Channel Skew	t _{PS}	For both co-directional and opposing direction		0.8	2.5	ns
Output Rise/Fall Time(8)	t _r , t _f	C _L =15pF		2.5	5	ns
Peak Eye Diagram Jitter ⁽¹⁰⁾	t _{JIT(PK)}			1.5		ns
Enable to Data Valid(11)	t _{EN-ON}			60	90	ns
Enable to Data Tri-State(11)	ten-off			50	75	ns
Input Power Fail to Valid Default Output	tsp			500		ns
Start-up Time	t start	From VDD1/VDD2 on to output valid		75		μs
Common-mode Transient Immunity ⁽¹⁰⁾	CMTI	IN=0V or VDD, V _{CM} = 1.5kV	±100			kV/µs
Power Supply Range						
Supply Voltage Range	V_{DD1}		2.5		5.5	V
Supply Voltage Kange	V_{DD2}		2.5		5.5	V
Under Voltage Lockout Threshold	V _{UVLO1-R}	V _{DD1} Rising		2.25		V
Officer Voltage Lockout Tilleshold	$V_{\text{UVLO2-R}}$	V _{DD2} Rising		2.25		V
Under Voltage Lockout Threshold	V _{UVHYS1}	V _{DD1}		200		mV
Hysteresis	V _{UVHYS2}	V _{DD2}		200		mV
Pin Input / Output Logic Threshold	t	,		T. T.		
Input Voltage High Threshold	V _{ITH-H}	INx, ENx pins			2	V
Input Voltage Low Threshold	V _{ITH-L}		0.8			V
Input Threshold Hysteresis	Vith-HYS			350		mV
Pin Input Current Leakage		Connect INx to VDDx or GNDx			±10	μA
Pin Input Current Leakage		Test ENx pins, ENx =0V	-10	-5		μA
Output High Voltage	V _{OH}	OUTx pins. IOUT=-4mA	V _{DDx} -0.4	V _{DDx} -0.2		V
Output Low Voltage	V_{OL}	OUTx pins. IOUT=4mA		0.2	0.4	V
Tristate (high-impedance) Output Leakage Current		Connect OUTx to VDDx or GNDx, ENx = GNDx.			±10	μA
Output Impedance ⁽¹²⁾	Zo	OUTx pins		50		Ω
Thermal Protection						
Thermal Shutdown Temperature	T _{SD}			150		°C
Thermal Shutdown Hysteresis	T _{HYS}			20		°C



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

ELECTRICAL CHARACTERISTICS (continued)

 $V_{DD1} = V_{DD2} = 5V$, $T_J = -40$ °C to 125°C(7), typical values are tested at $T_J = 25$ °C, unless otherwise noted.

Part Number	Parameter	Condition	Min	Тур	Max	Units
Power Supply Cu	urrent					•
DC Supply Curre	ent (INx = 0V or VDD)					
	VDD1 Current	INx = VDD		2.5	3.8	mA
MP27931	VDD1 Current	INx = 0		7.9	11.9	mA
WIP27931	VDD2 Current	INx = VDD		3.5	5.3	mA
	VDD2 Current	INx = 0	X = 0 7.9 11.9 mA X = VDD 3.5 5.3 mA X = 0 5.3 8.0 mA X = VDD 7.9 11.9 mA X = 0 2.5 3.8 mA X = VDD 5.3 8.0 mA	mA		
MP27931-L	VDD1 Current	INx = VDD		7.9	11.9	mA
		INx = 0		2.5	3.8	mA
WIF21931-L	VDD2 Current	INx = VDD		5.3	8.0	mA
		INx = 0		3.5	5.3	mA
1Mbps Supply C	urrent (INx = 500kHz	Square Wave, C _{LOAD} = 15	pF on All O	ıtputs)		
MP27931	VDD1 Current			5.3	7.9	mA
MP27931-L	VDD2 Current			4.6	6.8	mA
10Mbps Supply	Current (INx = 5MHz	Square Wave, C _{LOAD} = 15	pF on All Ou	tputs)		
MP27931	VDD1 Current			5.7	8.6	mA
MP27931-L	VDD2 Current			5.9	8.9	mA
100Mbps Supply	Current (INx = 50Mi	Hz Square Wave, $C_{LOAD} = 1$	15 pF on All	Outputs)		
MP27931	VDD1 Current			10.2	15.3	mA
MP27931-L	VDD2 Current			19.4	29.1	mA



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

ELECTRICAL CHARACTERISTICS (continued)

 $V_{DD1} = V_{DD2} = 3.3V$, $T_J = -40^{\circ}C$ to 125°C⁽⁷⁾, typical values are tested at $T_J = 25^{\circ}C$, unless otherwise noted.

Minimum Pulse Width	Parameter	Symbol	Condition	Min	Тур	Max	Units
Propagation Delay(®)	Switching Timing Characteristics				<u> </u>		•
Pulse Width Distortion	Minimum Pulse Width					5	ns
Propagation Delay Skew (8) Tesk(P-P) Channel-Channel Skew Tesk For both co-directional and opposing direction 0.8 2.5	Propagation Delay ⁽⁸⁾	t _{PLH} , t _{PHL}			14		ns
Channel Skew Chan	Pulse Width Distortion	PWD	t _{PLH} - t _{PHL}		1.5	4.5	ns
Channel-Channel Skew Les and opposing direction Class	Propagation Delay Skew (9)	t _{PSK(P-P)}				4.5	ns
Peak Eye Diagram Jitter(10)	Channel-Channel Skew	t _{PS}			0.8	2.5	ns
Enable to Data Valid(**1)	Output Rise/Fall Time(8)	t _r , t _f	C _L =15pF		2.5	5	ns
Enable to Data Tri-State(11)	Peak Eye Diagram Jitter(10)	t _{JIT(PK)}			1.5		ns
Input Power Fail to Valid Default Output Output Power Fail to Valid Default Output Start-up Time ItsTART From VDD1/VDD2 on to output valid IN=0V or VDD, VCM = 1.5kV ±100 Its IN=0V or VDD, VCM = 1.5kV Its IN=0V or VDD, VCM	Enable to Data Valid ⁽¹¹⁾	t _{EN-ON}			60	90	ns
Output tsp 500 Start-up Time tstart From VDD1/VDD2 on to output valid 75 Common-mode Immunity(10) Transient Immunity(10) Image: Immunity(10) the proper value output valid Power Supply Range VDD1 VCM = 1.5kV ±100 ±100 Under Voltage Range VDD1 VCM = 1.5kV ±2.5 5.5 Under Voltage Lockout Threshold VUVLO1-R VDD1 Rising 2.25 5.5 Under Voltage Lockout Threshold VUVLO1-R VDD1 Rising 2.25 2.25 Under Voltage Lockout Threshold VUVHYS1 VDD1 200 200 Under Voltage Lockout Threshold VUVHYS1 VDD1 200 200 Pin Input / Output Logic Threshold VITH-HY INX, ENX pins 2 Pin Input Voltage High Threshold VITH-HY INX, ENX pins 2 Input Voltage Low Threshold VITH-HYS 0.8 350 Pin Input Current Leakage Test ENX pins, ENX ON STAN STAN STAN STAN STAN STAN STAN STA	Enable to Data Tri-State(11)	t _{EN-OFF}			50	75	ns
START Output valid 75	•	tsp			500		ns
Minumity(10)	Start-up Time	t start			75		μs
Supply Voltage Range		CMTI		±100			kV/µs
Vode	Power Supply Range						
Under Voltage Lockout Threshold	Supply Voltage Bange	V_{DD1}		2.5		5.5	V
Under Voltage Lockout Threshold V _{UVLO2-R} V _{DD2} Rising 2.25	Supply Voltage Kange	V_{DD2}		2.5		5.5	V
Under Voltage Lockout Threshold Hysteresis	Under Voltage Leckout Threshold	V _{UVLO1-R}	V _{DD1} Rising		2.25		V
Hysteresis Vuvhys2 VDD2 200	Onder Voltage Lockout Threshold	$V_{\text{UVLO2-R}}$	V _{DD2} Rising		2.25		V
Pin Input / Output Logic Threshold Input Voltage High Threshold Input Voltage Low Threshold Input Voltage Low Threshold Input Threshold Hysteresis Input Threshold Hysteresis Vith-Hys Input Current Leakage Pin Input Current Leakage Pin Input Current Leakage Test ENx pins, ENx -10 -5 Output High Voltage Voh OUTx pins. IOUT=-4mA Output Low Voltage Voh OUTx pins. IOUT=4mA Tristate (high-impedance) Output Leakage Current Output Impedance(12) Output Impedance(12) Zo OUTx pins Toutput Not Voltage Voh OUTx pins Toutput Voltage So OUTx pins Toutput Voltage Toutput Voltage So OUTx pins Toutput Voltage Toutput Voltage Toutput Voltage So OUTx pins Toutput Voltage Toutput Voltage Toutput Voltage Toutput Vo	Under Voltage Lockout Threshold	V _{UVHYS1}	V _{DD1}		200		mV
Input Voltage High Threshold VITH-H Input Voltage Low Threshold VITH-L Input Threshold Hysteresis VITH-HYS Pin Input Current Leakage Pin Input Current Leakage Pin Input Current Leakage Test ENx pins, ENx = 0V Output High Voltage Voh OUTx pins. IOUT=-4mA Tristate (high-impedance) Output Leakage Current Connect OUTx to VDDx or GNDx. Connect OUTx to VDDx or GNDx. Connect OUTx to VDDx or GNDx, ENx = GNDx. Output Impedance(12) Zo OUTx pins 50 Thermal Protection	Hysteresis	V _{UVHYS2}	V _{DD2}		200		mV
Input Voltage Low Threshold VITH-L Input Threshold Hysteresis VITH-HYS Pin Input Current Leakage Pin Input Current Leakage Pin Input Current Leakage Test ENx pins, ENx = 0V Output High Voltage Voh OUTx pins. IOUT=-4mA Tristate (high-impedance) Output Leakage Current Output Impedance(12) Output Impedance(12) Zo OUTx pins Output Note Output Down or GNDx. Output Impedance(12) Zo OUTx pins Output Down Output Down or GNDx. Output Impedance(12) Zo OUTx pins Output Down Output Down or GNDx. Thermal Protection	Pin Input / Output Logic Threshold	t					
Input Threshold Hysteresis Pin Input Current Leakage Pin Input Current Leakage Connect INx to VDDx or GNDx Test ENx pins, ENx = 0V Output High Voltage Voh OUTx pins. IOUT=-4mA Output Low Voltage Vol OUTx pins. IOUT=4mA Tristate (high-impedance) Output Leakage Current Output Impedance(12) Output Impedance(12) Zo OUTx pins 350 ±10 -5 Connect INx to VDDx or GNDx -10 -5 OUTx pins. IOUT=-4mA VDDx-0.2 0.4 Connect OUTx to VDDx or GNDx, ENx = GNDx. Output Impedance(12) Zo OUTx pins 50 Thermal Protection	Input Voltage High Threshold	V_{ITH-H}	INx, ENx pins			2	V
Pin Input Current Leakage Pin Input Current Leakage Pin Input Current Leakage Test ENx pins, ENx -10 -5 Output High Voltage VoH OUTx pins. IOUT=-4mA VDDx-0.4 VDDx-0.2 Output Low Voltage VoL OUTx pins. IOUT=4mA O.2 O.4 Tristate (high-impedance) Output Leakage Current Output Impedance(12) Zo OUTx pins Thermal Protection	Input Voltage Low Threshold	V _{ITH-L}		0.8			V
Pin Input Current Leakage or GNDx Pin Input Current Leakage Test ENx pins, ENx = 0V Output High Voltage Voh OUTx pins. IOUT=-4mA VDDx-0.4 VDDx-0.2 Output Low Voltage Vol OUTx pins. IOUT=4mA 0.2 0.4 Tristate (high-impedance) Output Leakage Current Output Impedance(12) Zo OUTx pins 50 Thermal Protection	Input Threshold Hysteresis	Vith-HYS			350		mV
Output High Voltage V_{OH} OUTx pins. IOUT=-4mA V_{DDx} -0.4 V_{DDx} -0.2 Output Low Voltage V_{OL} OUTx pins. IOUT=4mA V_{DDx} -0.4 O.2 O.4 Tristate (high-impedance) Output Leakage Current V_{DDx} OUTx to VDDx or GNDx, ENx = GNDx. Output Impedance(12) V_{DDx} OUTx pins V_{DDx} OUTx pins V_{DDx} Output Impedance(12) V_{DDx} OUTx pins V_{DDx} OUTx pins V_{DDx} Output Impedance(12) V_{DDx} OUTx pins V_{DDx}	Pin Input Current Leakage					±10	μΑ
Output Low Voltage Vol OUTx pins. IOUT=4mA Tristate (high-impedance) Output Leakage Current Output Impedance(12) Thermal Protection OUTx pins. IOUT=4mA Connect OUTx to VDDx or GNDx, ENx = GNDx. 50 Thermal Protection	Pin Input Current Leakage			-10	-5		μA
Tristate (high-impedance) Output Leakage Current Connect OUTx to VDDx or GNDx, ENx = GNDx. Output Impedance ⁽¹²⁾ Zo OUTx pins 50 Thermal Protection	Output High Voltage	V _{OH}	OUTx pins. IOUT=-4mA	V _{DDx} -0.4	V _{DDx} -0.2		V
Leakage Current or GNDx, ENx = GNDx. ± 10 Output Impedance ⁽¹²⁾ Z_0 OUTx pins 50 Thermal Protection	Output Low Voltage	V _{OL}	OUTx pins. IOUT=4mA		0.2	0.4	V
Thermal Protection						±10	μA
	Output Impedance ⁽¹²⁾	Zo	OUTx pins		50		Ω
Thermal Shutdown Temperature T _{SD} 150	Thermal Protection				-		
	Thermal Shutdown Temperature	T _{SD}			150		°C
Thermal Shutdown Hysteresis T _{HYS} 20	Thermal Shutdown Hysteresis	T _{HYS}			20		°C



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

ELECTRICAL CHARACTERISTICS (continued)

 $V_{DD1} = V_{DD2} = 3.3V$, $T_J = -40^{\circ}C$ to 125°C⁽⁷⁾, typical values are tested at $T_J = 25^{\circ}C$, unless otherwise noted.

Part Number	Parameter	Condition	Min	Тур	Max	Units
Power Supply C	urrent					
DC Supply Curre	ent (INx = 0V or VDD)					
	VDD1 Current	INx = VDD		2.5	3.8	mA
MP27931	VDD1 Cullent	INx = VDD 2.5 INx = 0 7.9 INx = VDD 3.5 INx = VDD 7.9 INx = VDD 7.9 INx = VDD 5.3 INx = VDD 5.3 INx = VDD 5.3 INx = VDD 5.3 INx = VDD 5.2 4.5 4.5 5MHz Square Wave, $C_{LOAD} = 15 pF$ on All Outputs) 5.6 5.6 = 50MHz Square Wave, $C_{LOAD} = 15 pF$ on All Outputs)	11.9	mA		
WIP27931	VDD2 Current	INx = VDD		3.5	5.3	mA
	VDD2 Current	INx = 0	2.5 3.8 mA 7.9 11.9 mA 3.5 5.3 mA 5.3 8.0 mA 7.9 11.9 mA 2.5 3.8 mA 2.5 3.8 mA 5.3 8.0 mA 5.6 8.4 mA	mA		
MD07024 I	VDD1 Current	INx = VDD		7.9	11.9	mA
		INx = 0		2.5	3.8	mA
MP27931-L	VDD2 Current	INx = VDD		5.3	8.0	mA
		INx = 0		3.5	5.3	mA
1Mbps Supply C	Current (INx = 500kHz	Square Wave, C _{LOAD} = 15	pF on All O	utputs)		
MP27931	VDD1 Current			5.2	7.9	mA
MP27931-L	VDD2 Current			4.5	6.8	mA
10Mbps Supply	Current (INx = 5MHz	Square Wave, $C_{LOAD} = 15$	pF on All Ou	tputs)		
MP27931	VDD1 Current			5.6	8.4	mA
MP27931-L	VDD2 Current			5.6	8.4	mA
100Mbps Supply	Current (INx = 50Mi	Hz Square Wave, C _{LOAD} = 1	15 pF on All	Outputs)		
MP27931	VDD1 Current			9.3	14.0	mA
MP27931-L	VDD2 Current			16.7	25.1	mA



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

ELECTRICAL CHARACTERISTICS (continued)

 $V_{DD1} = V_{DD2} = 2.5V$, $T_J = -40^{\circ}C$ to $125^{\circ}C^{(7)}$, typical values are tested at $T_J = 25^{\circ}C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Switching Timing Characteristics				<u> </u>		
Minimum Pulse Width					5	ns
Propagation Delay ⁽⁸⁾	t _{PLH} , t _{PHL}			15		ns
Pulse Width Distortion	PWD	t _{PLH} - t _{PHL}		1.5	4.5	ns
Propagation Delay Skew (9)	t _{PSK(P-P)}				4.5	ns
Channel-Channel Skew	t _{PS}	For both co-directional and opposing direction		0.8	2.5	ns
Output Rise/Fall Time(8)	t _r , t _f	C _L =15pF		2.5	5	ns
Peak Eye Diagram Jitter ⁽¹⁰⁾	t _{JIT(PK)}			1.5		ns
Enable to Data Valid ⁽¹¹⁾	ten-on			60	90	ns
Enable to Data Tri-State(11)	ten-off			50	75	ns
Input Power Fail to Valid Default Output	tsp			500		ns
Start-up Time	t start	From VDD1/VDD2 on to output valid		75		μs
Common-mode Transient Immunity ⁽¹⁰⁾	CMTI	IN=0V or VDD, V _{CM} = 1.5kV	±100			kV/µs
Power Supply Range						
Supply Voltage Range	V_{DD1}		2.5		5.5	V
Supply Voltage Kange	V_{DD2}		2.5		5.5	V
Under Voltage Lockout Threshold	V _{UVLO1-R}	V _{DD1} Rising		2.25		V
Onder Voltage Lockout Threshold	$V_{\text{UVLO2-R}}$	V _{DD2} Rising		2.25		V
Under Voltage Lockout Threshold	V _{UVHYS1}	V _{DD1}		200		mV
Hysteresis	V _{UVHYS2}	V _{DD2}		200		mV
Pin Input / Output Logic Threshold	t					
Input Voltage High Threshold	V_{ITH-H}	INx, ENx pins			2	V
Input Voltage Low Threshold	V _{ITH-L}		0.8			V
Input Threshold Hysteresis	Vith-HYS			350		mV
Pin Input Current Leakage		Connect INx to VDDx or GNDx			±10	μΑ
Pin Input Current Leakage		Test ENx pins, ENx =0V	-10	-5		μA
Output High Voltage	V _{OH}	OUTx pins. IOUT=-4mA	V _{DDx} -0.4	V _{DDx} -0.2		V
Output Low Voltage	V _{OL}	OUTx pins. IOUT=4mA		0.2	0.4	V
Tristate (high-impedance) Output Leakage Current		Connect OUTx to VDDx or GNDx, ENx = GNDx.			±10	μA
Output Impedance ⁽¹²⁾	Zo	OUTx pins		50		Ω
Thermal Protection				'		•
Thermal Shutdown Temperature	T _{SD}			150		°C
Thermal Shutdown Hysteresis	T _{HYS}			20		°C



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

ELECTRICAL CHARACTERISTICS (continued)

 $V_{DD1} = V_{DD2} = 2.5V$, $T_J = -40^{\circ}C$ to 125°C⁽⁷⁾, typical values are tested at $T_J = 25^{\circ}C$, unless otherwise noted.

Part Number	Parameter	Condition	Min	Тур	Max	Units
Power Supply C	urrent					•
DC Supply Curre	ent (INx = 0V or VDD))				
	VDD1 Current	INx = VDD		2.5	3.8	mA
MD27024	VDDT Current	INx = 0		7.9	11.9	mA
MP27931	VDD2 Current	INx = VDD		3.5	5.3	mA
	VDD2 Current	INx = 0		5.3	8.0	mA
	VDD1 Current	INx = VDD		7.9	11.9	mA
MP27931-L	VDD1 Current	INx = 0		2.5	3.8	mA
WIF27931-L	VDD2 Current	INx = VDD		5.3	8.0	mA
		INx = 0		3.5	5.3	mA
1Mbps Supply C	Current (INx = 500kHz	z Square Wave, $C_{LOAD} = 15$	pF on All Ou	ıtputs)		
MP27931	VDD1 Current			5.2	7.8	mA
MP27931-L	VDD2 Current			4.5	6.7	mA
10Mbps Supply	Current (INx = 5MHz	Square Wave, C _{LOAD} = 15	pF on All Ou	tputs)		
MP27931	VDD1 Current			5.5	8.3	mA
MP27931-L	VDD2 Current			5.3	8.0	mA
100Mbps Supply	Current (INx = 50M	Hz Square Wave, C _{LOAD} =	15 pF on All	Outputs)		
MP27931	VDD1 Current			8.2	12.3	mA
MP27931-L	VDD2 Current			13.4	20.1	mA

Notes:

- 7) Not tested in production, derived by over-temperature correlation.
- 8) Refer to Figure 4.
- 9) t_{PSK(P-P)} is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.
- 10) Derived by sample characterization, not tested in production.
- 11) Refer to Figure 6.
- 12) The nominal output impedance of an isolator driver channel is approximately 50Ω±40%, which is a combination of the value of the on-chip series termination resistor and channel resistance of the output driver FET. When driving loads where transmission line effects will be a factor, output pins should be appropriately terminated with controlled-impedance PCB traces.



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

REGULATORY INFORMATION

UL	CSA	VDE(IEC)	cqc
Certified according to UL1577 Component Recognition Program	Certified according to CSA Component Acceptance Service Notice No.5A	Certified according to DIN EN IEC 60747-17 (VDE 0884-17): 2021-10; EN IEC 60747-17:2020 + AC:2021	Certified according to GB4943.1-2011
SOIC-16 WB Package: Single protection, 5000V _{RMS}	SOIC-16 WB Package: Single protection, 5000V _{RMS}	Basic isolation: Maximum transient isolation voltage, 7071 V _{PK} Maximum repetitive peak isolation voltage, 1200 V _{PK} Maximum surge isolation voltage, 3077 V _{PK}	Altitude ≤ 5000m, Tropical Climate, Reinforced insulation 600V _{RMS} Maximum working voltage Basic insulation 1000V _{RMS} Maximum working voltage
File (E322138)	File (E322138)	File (Pending)	File (Pending)

Notes:

INSULATION SPECIFICATIONS

Parameter	Symbol	Condition	SOIC-16 WB	Units
External Clearance (14)	CLR	According to IEC 60664-1(VDE 0110-1) Shortest pin-to-pin distance through air between primary and secondary side	>8	mm
External Creepage (14)	CPG	According to IEC 60664-1(VDE 0110-1) Shortest pin-to-pin distance across the package surface between primary and secondary side	>8	mm
Minimum Internal Gap	DTI	Internal Clearance	>20	μm
Tracking Resistance (Comparative Tracking Index)	СТІ	According to IEC 60112	>600	V _{RMS}
Material Group		According to IEC 60664-1	I	
Overveltage Category		Rated mains voltages ≤ 150V _{RMS}	I-IV	
Overvoltage Category per IEC 60664-1		Rated mains voltages ≤ 300V _{RMS}	I-IV	
per 1EC 00004-1		Rated mains voltages ≤ 600V _{RMS}	1-111	

Notes:

¹³⁾ Regulatory Certification apply to 5000V_{RMS} rated devices which are production tested to 6000V_{RMS} for 1 second. Regulatory Certification apply to 3750V_{RMS} rated devices which are production tested to 4500V_{RMS} for 1 second,

¹⁴⁾ Refer to package information for detailed dimensions. As isolated solution, the recommended land pattern is helpful to keep enough safety creepage and clearance distances on a printed-circuit board.



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

INSULATION CHARACTERISTICS

Parameter	Symbol	Condition	SOIC-16 WB	Units
UL 1577, 5 th Ed				
Isolation Voltage Rating	Viso	V _{TEST} =V _{ISO} , t=60s, (Qualification Test) V _{TEST} =V _{ISO} × 1.2, t=1s, (100% Production Test)	5000	V _{RMS}
DIN EN IEC 60747-17 (VI	DE 0884-17)	: 2021-10		
Maximum Working Isolation Voltage	Viorm		1200	VPEAK
Apparent Charge (15)	Q pd	Method B1. routine test $V_{pd(m)} = 1.875 \times V_{IORM}$, $t_m = 1s$, (100% Production Test)	<5	pC
		Method A, after sample test. And subgroup1 $V_{pd(m)}=V_{IORM}\times 1.3,\ t_{m}=10s,$ After type test subgroup2/3 $V_{pd(m)}=V_{IORM}\times 1.2,\ t_{m}=10s,$ (Qualification Test)	<5	pC
Transient Overvoltage	Vютм	VTEST=VIOTM for t=60s (Qualification Test) VTEST=VIOTM x 1.2 for t=1s (100% Production Test)	7071	VPEAK
Maximum Surge Isolation Voltage	Viosm	Tested with surge waveform 1.2µs/50µs . V _{TEST} =V _{ISOM} × 1.3 (Qualification Test)	3077	VPEAK
Barrier Capacitance (16)	C _{IO}	f=1MHz	2	pF
Insulation Resistance (16) R _{IO}		V _{IO} =500V, T _A =25°C V _{IO} =500V, 100°C≤T _A ≤125°C V _{IO} =500V, T _A =T _S =150°C	>10 ¹² >10 ¹¹ >10 ⁹	Ω Ω Ω
Pollution Degree Climatic Category			2 40/125/21	

Notes:

SAFETY LIMITING VALUES (17)

Parameter	Symbol	Condition	SOIC-16 WB	Units
Maximum Safety Temperature (18)	Ts		150	°C
Safety input, output, or supply current	Is	V _{DD} = 5.5 V, T _J = 150°C, T _A = 25°C	400	mA
Safety input, output, or total power (19)	Ps	T _J = 150°C, T _A = 25°C	2200	mW

Notes:

- 17) Maximum value allowed in the event of a failure.
- 18) The maximum safety temperature T_S has the same value as the maximum junction temperature T_J (MAX) specified in ABSOLUTE MAXIMUM RATINGS.
- 19) The safety power dissipation is a function of the maximum junction temperature TJ (MAX), the junction-to-ambient thermal resistance $\theta_{\rm JA}$ and the ambient temperature TA:

 $T_S=T_J (MAX)=T_A+(\theta_{JA} \times P_S)$

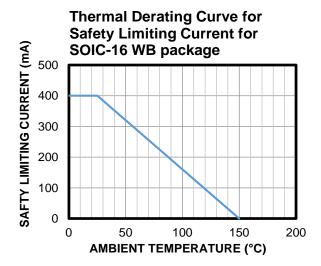
¹⁵⁾ Electrical discharge caused by a partial discharge in the coupler.

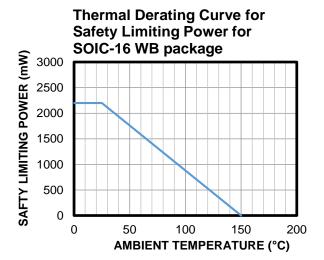
¹⁶⁾ The primary side terminals as well as the secondary side terminals of the barrier are connected together forming a two-terminal device. Then C_{IO} and R_{IO} are measured between the two terminals of the coupler.



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

THERMAL DERATING CURVE FOR SAFETY LIMITING VALUES







PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

TYPICAL PERFORMANCE CHARACTERISTICS

Performance waveforms are tested on the evaluation board in the Design Example section on Page xx. $V_{DD1} = V_{DD2} = 5V$, INA / INB / INC / IND = 5MHz square waveform, $T_A = 25$ °C, unless otherwise noted.

TBD



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

FUNCTIONAL BLOCK DIAGRAM

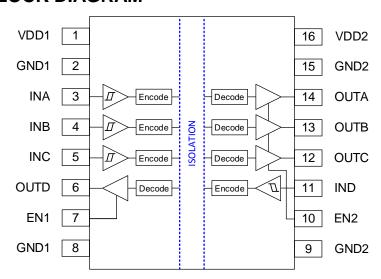


Figure 1: Functional Block Diagram

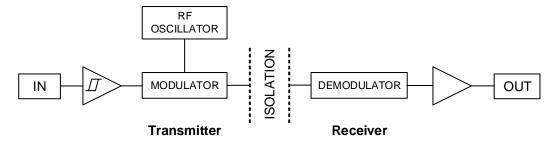


Figure 2: Isolated Signal Modulation Diagram



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

OUTPUT TRUTH TABLE

Table 1: Truth Table

IN SIDE VDD	OUT SIDE VDD	OUT SIDE EN	IN	OUT			
Normal work state:							
Powered	Powered	H or FLOAT	Н	Н			
Powered	Powered	H or FLOAT	L	L			
Powered	Powered	H or FLOAT	FLOAT	H for MP27931 L for MP27931-L			
EN off state							
X	Powered	L	X	Hi-Z			
Input side powers off state:							
Un-powered ⁽²⁰⁾	Powered	H or FLOAT	Х	H for MP27931 L for MP27931-L			
Output side powers off state:							
Х	Un-powered ⁽²⁰⁾	X	X	1			

Hi-Z = high impendence, X = do not care, FLOAT = not connected, I = indeterminate, H = high level voltage, L = low level voltage

Notes:

²⁰⁾ An I/O can power the die for a given side through an internal diode if its source has adequate current.



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

OPERATION

The MP27931 is a 4 channels digital isolator optimized to replacing traditional opto-coupler isolation in application. It adopts capacitive isolation technology, supporting up to 5kVrms insulation voltage rating and up to 150Mbps data rate transmission.

Signal Isolation Function

MP27931 supports 5kVrms voltage isolation between two sides. Data signals applied on INx pins are transmitted to corresponding OUTx through internal isolation barrier. Figure 1 shows the IC diagram and Figure 2 shows isolated signal transmission structures.

Each signal channel consists of an RF transmitter and RF receiver separated by a semiconductor-based isolation barrier, on input port, the transmitter modulates the signal through an RF oscillator. When input signal is high, the RF oscillator keeps off. When input signal is low, the RF oscillator keeps on. On receiver side, a demodulator decodes the input state according to its RF energy content and applies the result to output pin. This signal modulation provides low power consumption and improved immunity to magnetic fields. Figure 3 shows the modulation scheme.

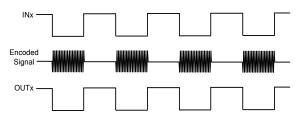


Figure 3: Signal Modulation Scheme

All channel signals have schmitt trigger input to enhance noise immunity. At the same time, all channels in one direction are optimized for propagation delay matching, which means they have similar delay time in one chip. It can be used for SPI interface isolation with good channel-channel skew.

Fail-safe Operation

MP27931 default output is high (MP27931-L default output is low) when the input power supply is not applied. With this fail-safe predetermined output, dc correctness is ensured in the absence of input logic transitions. So MP27931 can be

used for SPI interface isolation while slave device is not selected at power failure status.

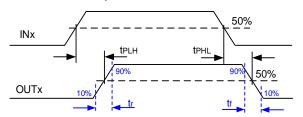


Figure 4: Propagation Delay Time

Power Supply

Both the VDD1 and VDD2 have an under-voltage lockout (UVLO) function to prevent erroneous operation during device startup & shutdown, or when the corresponding VDD is low.

Outputs are high impedance during power-up until the corresponding VDD is above the UVLO threshold for time period t_{START} . After this period, the outputs follow the state of inputs. Figure 5 shows the UVLO delay function.

Each side can enter or exit UVLO independently. While the output state is different. For example, when VDD1 enters UVLO, side 2 output will keep high if VDD2 is on. But when VDD2 enters in UVLO, side 2 output will be high impedance even VDD1 is on. This feature can prevent outputs wrong flip during VDD startup. Figure 5 shows the operation.

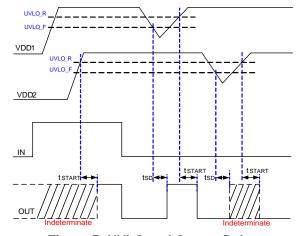


Figure 5: UVLO and Output Delay



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

EN Pin Control

MP27931 has one EN pin on each side of the isolation barrier, theses pins only control the output driver of each channel. When EN is high or floats, the OUT signal follows IN signal. When EN is low, the OUT runs into high-impedance state. Enable inputs EN1 and EN2 can be used for multiplexing, clock sync, or other output control. It is recommended that the enable inputs be connected to an external logic high or low level when the IC is operating in noisy environments. To minimize noise coupling, do not connect circuit traces to EN1 or EN2 if they are left floating.

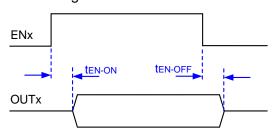


Figure 6: Enable Delay Time

Driver Output Protection

When the driver pin outputs over load or short to GND, one internal current limit circuit prevents the current from running too high. And if the die temperature is too high due to the high current, it will trigger thermal protection.

Thermal Protection

MP27931 has over temperature protection function in case the power dissipation during fault conditions. This thermal protection circuit disables the driver outputs when a die temperature rise to 150°C, There is about 20°C hysteresis. Once the junction temperature drops to about 130°C, the driver outputs are re-enabled work normally.



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

APPLICATION INFORMATION

Bypass Capacitor

A 0.1µF capacitor is recommended to ensure reliable propagation. Bypass capacitor should be placed as close to power supply and ground pins as possible.

Design Example

Table 2 is a design example following the application guidelines for the specifications below.

Table 2: Design Example

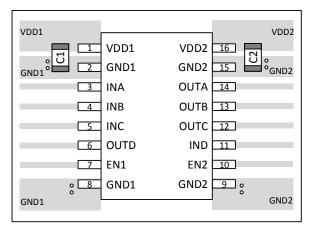
V_{DD1}	2.5-5.5V
V_{DD2}	2.5-5.5V

The detailed application schematic is shown in Figure 8. The typical performance and circuit waveforms are shown in the **Typical** Performance Characteristics section. For more device applications, please refer to the related evaluation board datasheet.

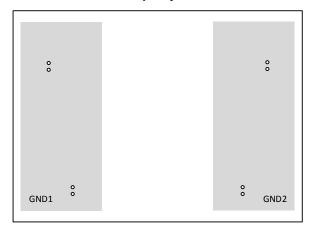
PCB Layout Guidelines

PCB layout is very important for normal operation. Refer to below layout guide lines.

- 1) For safety concern, primary side and secondary side must be physically separated. And the creepage/clearance must meet the standard for a certain application.
- 2) Minimize the loop area between signal traces and GND to avoid coupling noise into system. Keep signal traces away from other high speed traces or switching node, such as transformer, power inductor and MOS.
- 3) Two ceramic input decoupling capacitors need to be placed as close as possible to the VDD1 and GND1, VDD2 and GND2 pins.
- 4) For high speed signal, a four layers PCB is recommended to accomplish better EMI and signal propagation performance. Layer stacking: high speed signal, solid GND plane, VDD plane, low frequency signal.



Top Layer



Bottom Layer

Figure 7: Recommended PCB Layout



PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

TYPICAL APPLICATION CIRCUITS

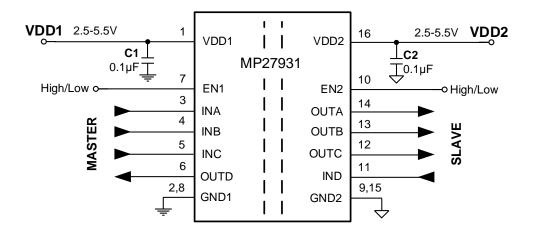


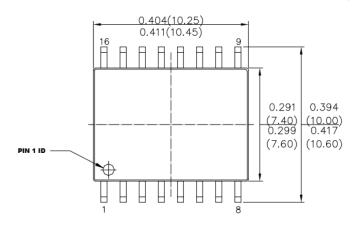
Figure 8: 4 Channels (Channel Direction: 3 Forward 1 Reverse) Isolated Interface

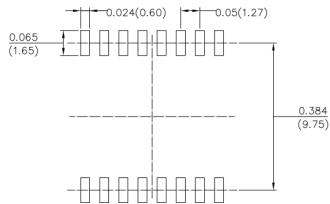


PRELIMINARY SPECIFICATIONS SUBJECT TO CHANGE

PACKAGE INFORMATION

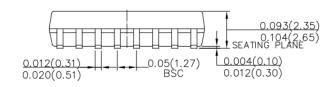
SOIC-16 WB (HV ISOLATION)

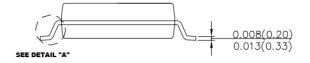




TOP VIEW

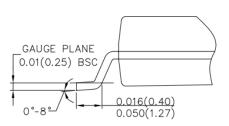
RECOMMENDED LAND PATTERN





FRONT VIEW

SIDE VIEW



DETAIL "A"

NOTE:

- 1) CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
- 2) PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 3) PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- 4) LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
- 5) DRAWING CONFORMS TO JEDEC MS-013, VARIATION AA.
- 6) DRAWING IS NOT TO SCALE.

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